

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 251996US2		SERIAL NO. 10/824535 New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Tomoaki SHINO			
				FILING DATE Herewith 4/15/04		GROUP 2811	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
A.O.A.	AA	6,538,916	03/25/03	Takashi OHSAWA			
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION		
					YES	NO	
A.O.A.	AO	2002-246571	08/30/02	Japan (with English Abstract and Corresponding U.S. Patent 6,538,916)		x	
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
A.O.A.	AW	Takashi OHSAWA, et al., "Memory Design Using a One-Transistor Gain Cell on SOI", IEEE JOURNAL OF SOLID-STATE CIRCUITS, Vol. 37, No. 11, November 2002, pgs. 1510-1522					
	AX						
	AY						
	AZ					<input type="checkbox"/> Additional References sheet(s) attached	
Examiner <i>am o. am</i>					Date Considered 1 July 05		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

CLASS
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CLASS